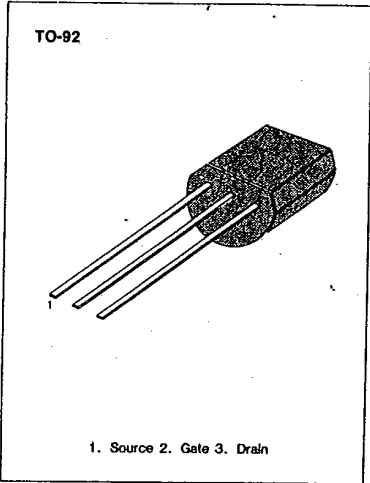


**KSK30**

**SILICON N-CHANNEL JUNCTION FET**

**LOW NOISE PRE-AMP. USE**

High Input Impedance:  $I_{gss} = 1nA$  (MAX)  
 Low Noise:  $NF = 0.5dB$  (TYP)  
 High Voltage:  $V_{gds} = -50V$



**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Rating	Unit
Gate-Drain Voltage	$V_{gds}$	-50	V
Gate Current	$I_g$	10	mA
Collector Dissipation	$P_C$	100	mW
Junction Temperature	TJ	125	$^\circ C$
Storage Temperature	Tstg	-55~125	$^\circ C$

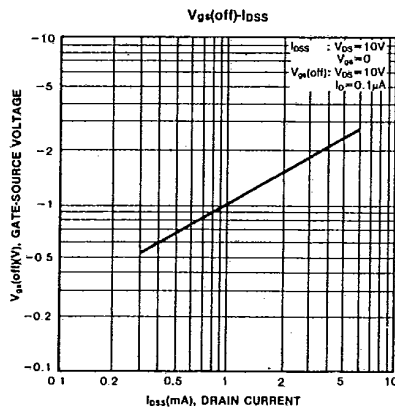
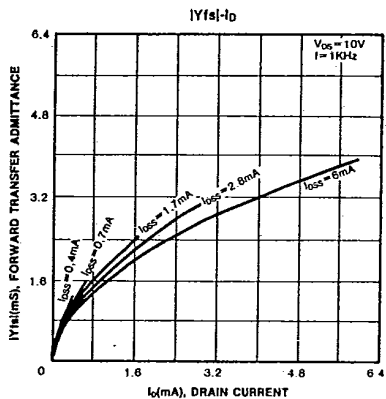
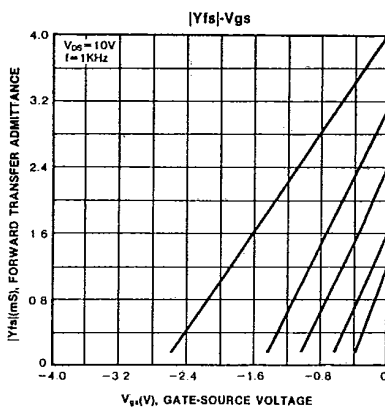
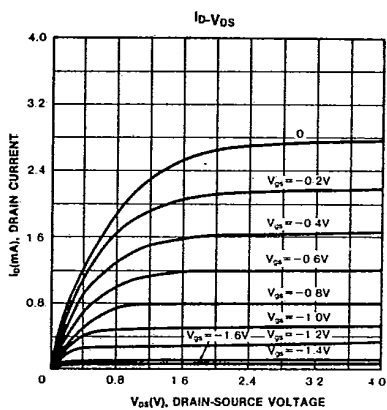
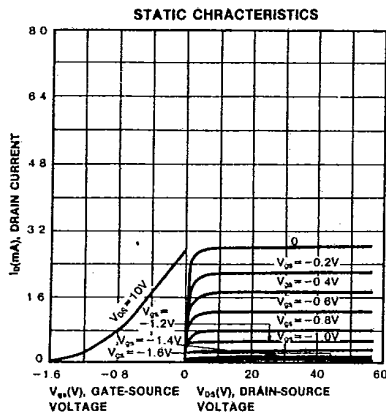
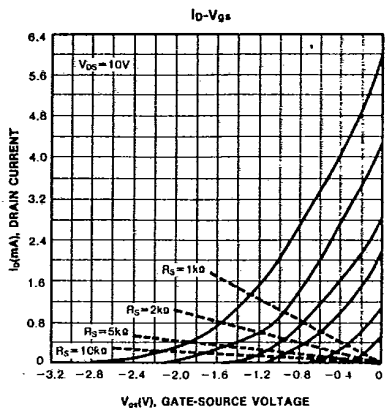
**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Gate-Drain Breakdown Voltage	$BV_{gds}$	$V_{DS} = 0, I_g = -100\mu A$	-50			V
Gate Leak Current	$I_{gss}$	$V_{gs} = -30V, V_{DS} = 0$			-1	nA
Drain Leak Current	$I_{DSS}$	$V_{DS} = 10V, V_{GS} = 0$	0.3		6.5	mA
Gate-Source Voltage	$V_{gs(off)}$	$V_{DS} = 10V, I_D = 0.1\mu A$	-0.4		-5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, V_{GS} = 0, f = 1KHz$	1.2			mS
Input Capacitance	$C_{iss}$	$V_{DS} = 0, V_{GS} = 0, f = 1MHz$		8.2		pF
Feedback Capacitance	$C_{rss}$	$V_{gs} = -10V, V_{DS} = 0$ $f = 1MHz$		2.6		pF
Noise Figure	NF	$V_{DS} = 15V, V_{GS} = 0$ $R_G = 100k\Omega$ $f = 120Hz$		0.5	5	dB

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**$I_{DSS}$  CLASSIFICATION**

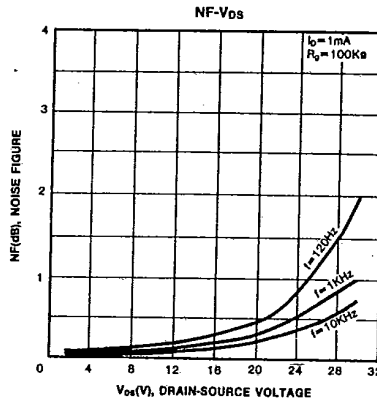
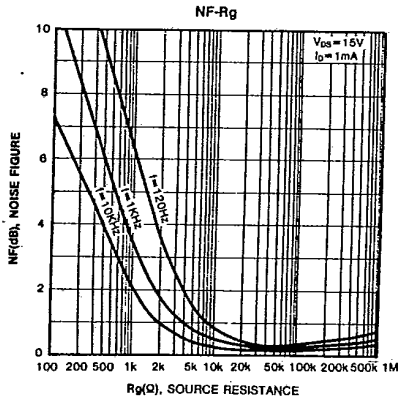
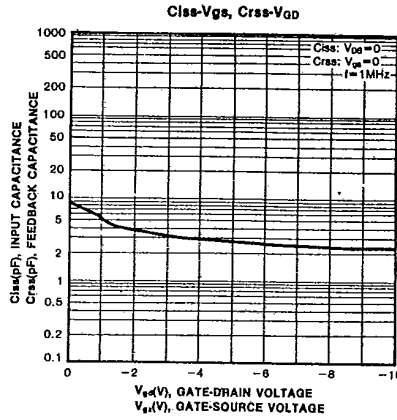
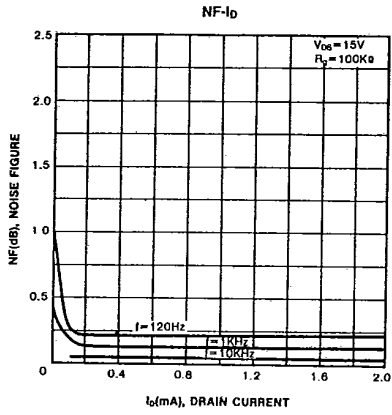
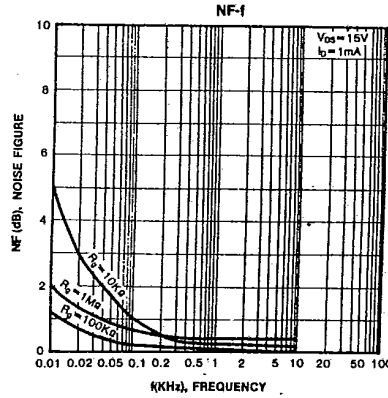
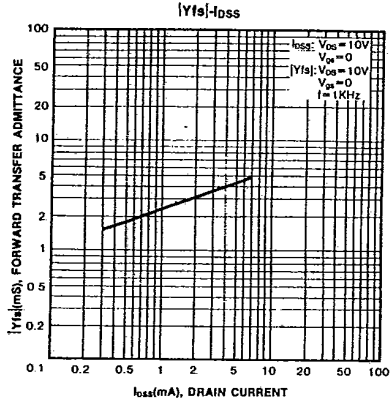
Classification	R	O	Y	G
$I_{DSS}(mA)$	0.30-0.75	0.60-1.40	1.20-3.00	2.60-6.50



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SILICON N-CHANNEL JUNCTION FET

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